PSF30065H

650V 30A 100mΩ Si Super junction MOSFET with Fast Recovery diode

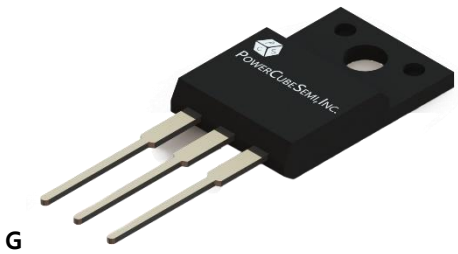
Features

Si Super junction MOSFET

- Rated to 650V at 30Amps @T_C = 25℃
- Max $R_{DS(on)}$ = 100 mΩ
- Typ $R_{DS(on)}$ = 90 mΩ
- Improved dv/dt Capability
- 100% Avalanche Tested

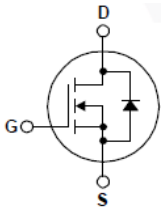
Application

- Solar inverters
- LCD/LED/PDP TV
- Telecom/Server Power supplies
- AC-DC Power Supply



G D S

PKG type : TO-220F-3L



Halogen-Free

RoHS

Description

PSF30065H is PowerCubeSemi's second generation of high voltage Super Junction MOSFET with FRD that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, the combination of Super Junction MOSFET with FRD is suitable for various AC/DC power conversion for system miniaturization and higher efficiency

Absolute Maximum Ratings

Symbol	Parameter	Test Condition	Value	Unit
BV_{DSS}	Drain-source breakdown Voltage	V_{GS}=0V, I_D=1mA	650	V
I_D	Drain current	T_c=25℃	30	A
I_{DM}	Pulsed Drain current	Pulse width limited by junction temperature	105	A
V_{GS}	Gate-source voltage		±30	V
E_{AS}	Single pulsed avalanche energy	I_D=6.2A, V_{DD}=50V	1250	mJ
P_d	Power dissipation	T_C=25℃	32.9	W
T_J	Operating Junction Temperature		150	℃
T_{stg}	Storage temperature		-55 to 150	℃

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Tape width	Quantity
PSF30065H	PSF30065	TO-220F-3L	TUBE	-	50

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical			Unit
			Min	Typ.	Max.	
BV_{DSS}	Drain-source breakdown voltage	V_{GS} = 0V, I_D = 1mA, T_J = 25°C	650	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 650V, V_{GS} = 0V	-	-	10	μA
I_{GSS}	Gate-source leakage current	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} =V_{GS}, I_D = 1mA	3	-	5	V
$R_{DS(ON)}$	Static drain-source on state resistance	V_{GS} = 10V, I_D = 15A	-	90	100	mΩ
$t_{d(on)}$	Turn-on Delay time	V_{DD} = 380V, I_D = 15A, V_{GS} = 10V, R_G = 10Ω	-	86	-	ns
T_r	Turn-on Rise time		-	9	-	
$t_{d(off)}$	Turn-off Delay time		-	130	-	
T_f	Turn-off Fall time		-	4.5	-	

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$R_{\theta JC}$	Thermal resistance, Junction to case		3.8	-	℃/W
R_g	Gate resistance	V_{GS} = 0V, f = 1.0㎒	1.3	-	Ω
C_{iss}	Input capacitance	V_{DS} = 380V, V_{GS} = 0V, f = 200㎑	3100	-	pF
C_{oss}	Output capacitance		67	-	
C_{rss}	Reverse transfer capacitance		5	-	
$Q_{g(tot)}$	Total gate charge at 10V	V_{DS} = 380V, I_D = 15A $V_{GS(on)}$ = 10V, $V_{GS(off)}$ = 0V	68	-	nC
Q_{gs}	Gate to source gate charge		14	-	nC
Q_{gd}	Gate to drain "Miller" charge		25	-	nC

Electrical Characteristics of Si Diode

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
I_S	Maximum continuous diode forward current		-	30	A
V_{SD}	Diode forward voltage	I_S = 15A, V_{GS} = 0V	-	1.3	V
T_{rr}	Reverse recovery time	I_{SD} = 15A, V_{DD} = 400V, dI_F/dt=100A/㎲	185	-	ns
Q_{rr}	Reverse recovery charge		1.4	-	μC
I_{rrm}	Reverse recovery current		16	-	A

Typical Characteristics

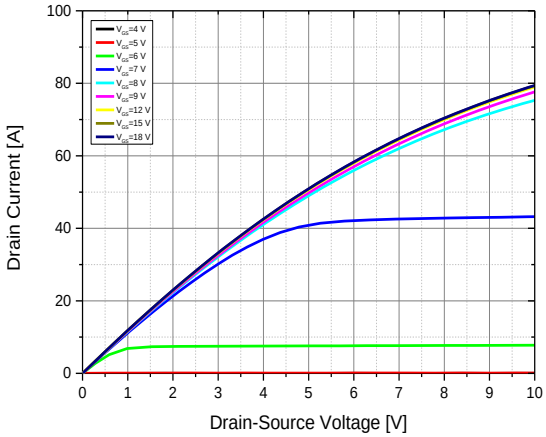


Figure 1. On-state characteristics

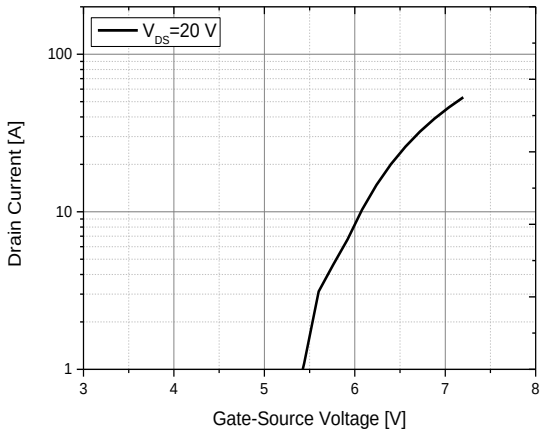


Figure 2. Transfer characteristics

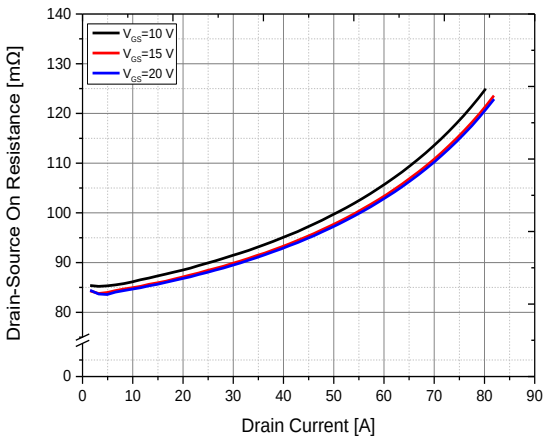


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

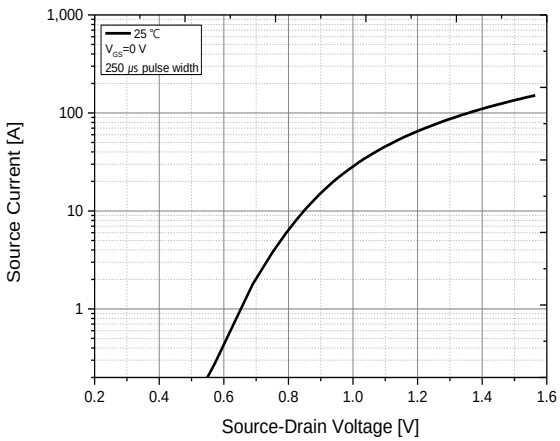


Figure 4. Body Forward Voltage Variation vs Source Current and Temperature

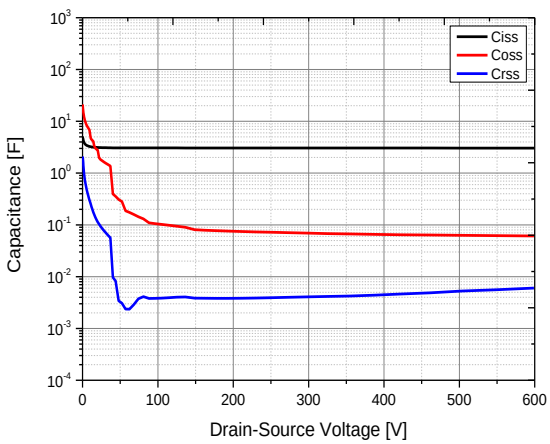


Figure 5. Capacitance Characteristics

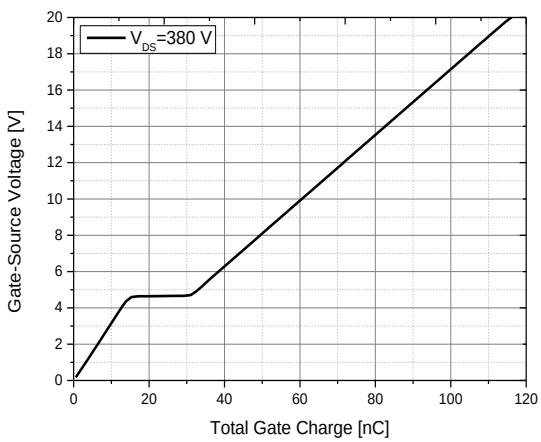


Figure 6. Gate Charge Characteristics

Typical Characteristics

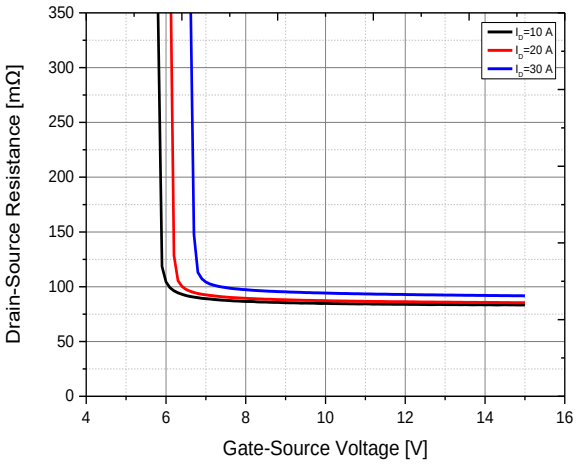


Figure 7. Drain to Source Resistance vs Gate to Source Voltage

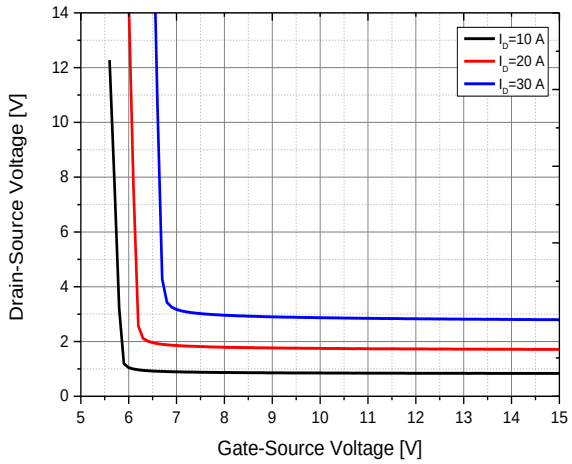


Figure 8. Drain to Source Voltage vs Gate to Source Voltage

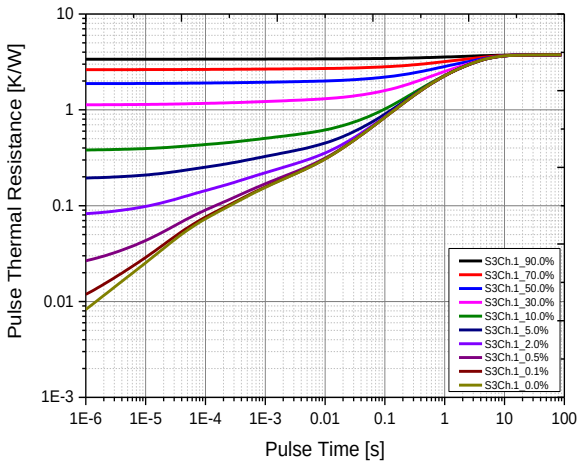


Figure 9. Transient thermal response curve

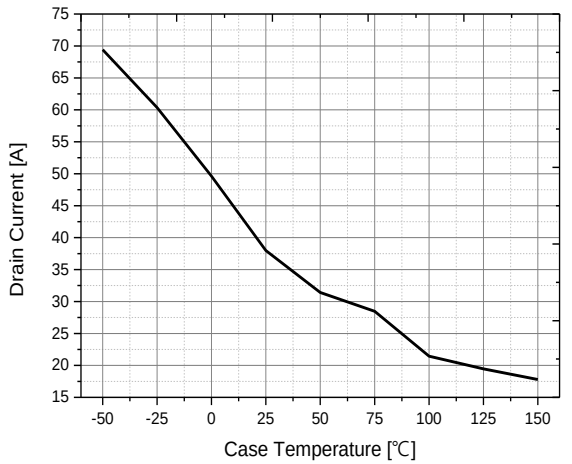


Figure 10. Case Temperature vs Drain Current

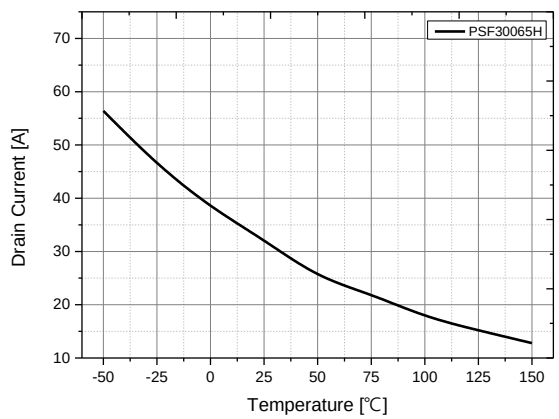
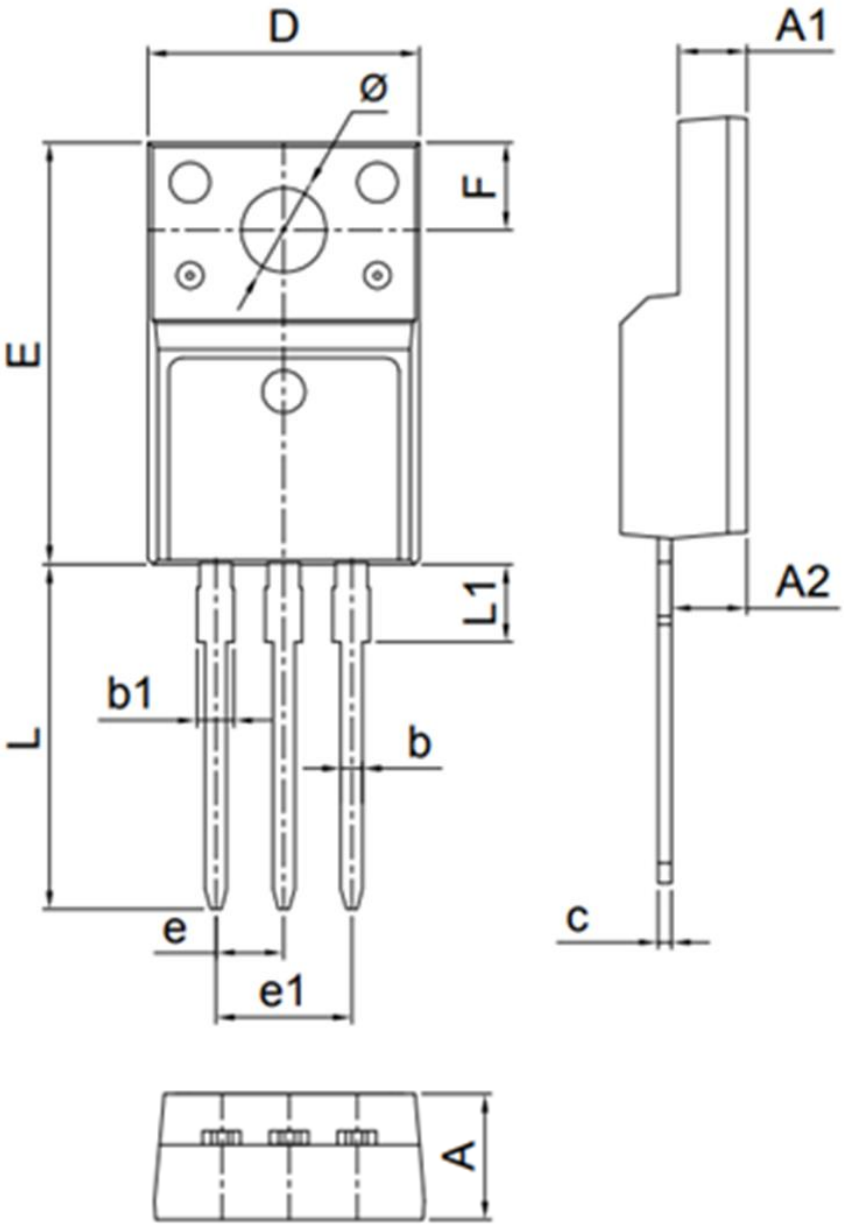


Figure 11. Drain Current vs. Temperature

Package Outline

[Unit : mm]



SYMBOL	DIMENSIONS	
	MIN	MAX
A	4.50	4.90
A1	2.34	2.74
A2	2.66	2.86
b	0.75	0.85
b1	1.24	1.44
c	0.40	0.60
D	10.00	10.32
E	15.75	16.05
e	2.44	2.64
e1	4.88	5.26
F	3.1	3.5
L	12.90	13.50
L1	2.90	3.30
Φ	3.10	3.30